



Features

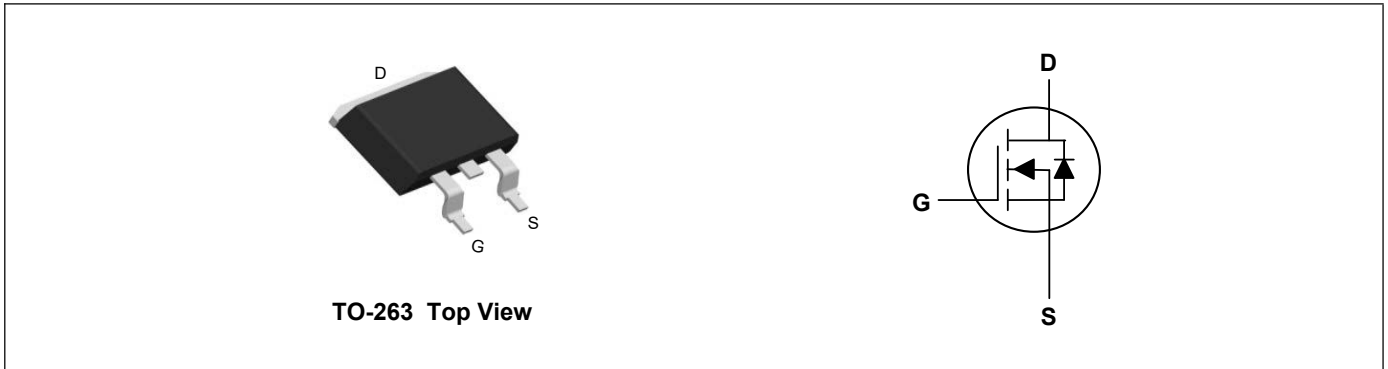
- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summary

V_{DS}	100	V
I_D	85	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	8.5	m Ω

Applications

- High Frequency Point-of-Load, Synchronous Buck Converter for
- Networking DC-DC Power System
- Load Switch



Absolute Maximum Ratings ($T_A=25^{\circ}C$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, V_{GS} @ 10V	$I_D@T_C=25^{\circ}C$	85	A
Continuous Drain Current, V_{GS} @ 10V	$I_D@T_C=100^{\circ}C$	53	A
Pulsed Drain Current ²	I_{DM}	340	A
Single Pulse Avalanche Energy ³	EAS	205	mJ
Avalanche Current	I_{AS}	64	A
Total Power Dissipation ⁴	$P_D@T_C=25^{\circ}C$	154	W
Storage Temperature Range	T_{STG}	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	T_J	-55 to 150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	62	$^{\circ}C/W$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	0.8	$^{\circ}C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	100	---	---	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =15A	---	6.8	8.5	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	2.0	---	4.0	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	5	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =10V, I _D =3A	---	10	---	S
Gate Resistance	R _g	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.1	---	Ω
Total Gate Charge	Q _g	V _{DS} =50V, V _{GS} =10V, I _D =40A	---	31	---	nC
Gate-Source Charge	Q _{gs}		---	10	---	
Gate-Drain Charge	Q _{gd}		---	11	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =50V, V _{GS} =10V, R _G =6Ω, I _D =40A	---	15	---	ns
Rise Time	T _r		---	33	---	
Turn-Off Delay Time	T _{d(off)}		---	60	---	
Fall Time	T _f		---	28	---	
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHz	---	1950	---	pF
Output Capacitance	C _{oss}		---	430	---	
Reverse Transfer Capacitance	C _{rss}		---	4.8	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ¹	I _S		---	---	85	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
Reverse Recovery Time	t _{rr}	I _F =10A, di/dt=100A/μs, T _J =25°C	---	240	---	nS
Reverse Recovery Charge	Q _{rr}		---	480	---	nC

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=50V, V_{GS}=10V, L=0.1mH
- 4.The power dissipation is limited by 150°C junction temperature

Typical Characteristics

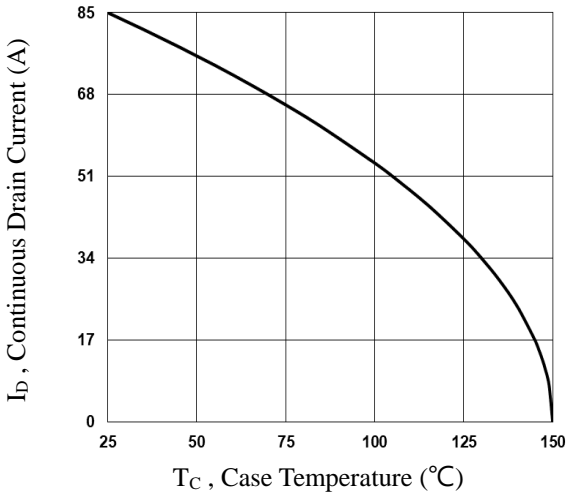


Fig.1 Continuous Drain Current vs. T_c

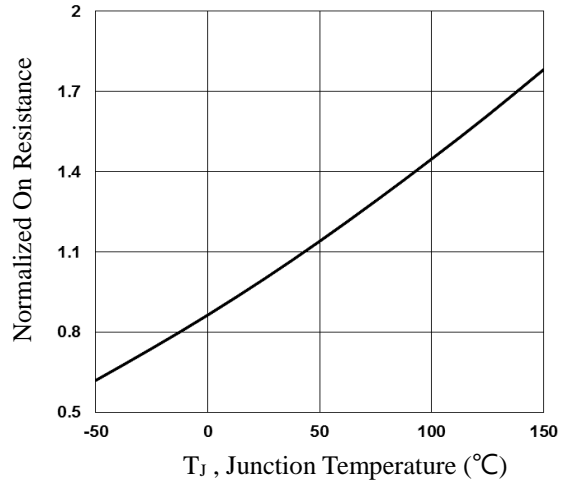


Fig.2 Normalized R_{DS(on)} vs. T_j

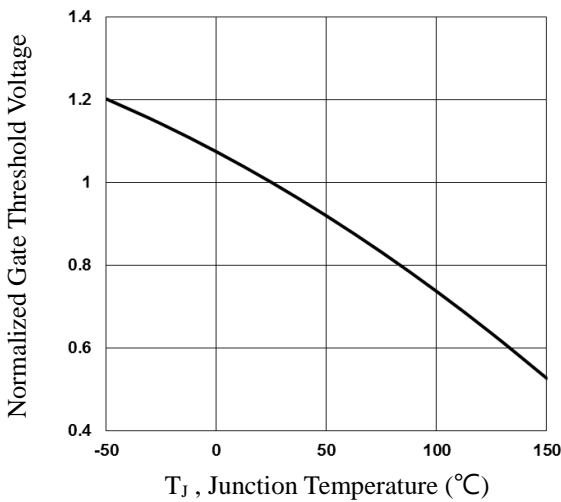


Fig.3 Normalized V_{th} vs. T_j

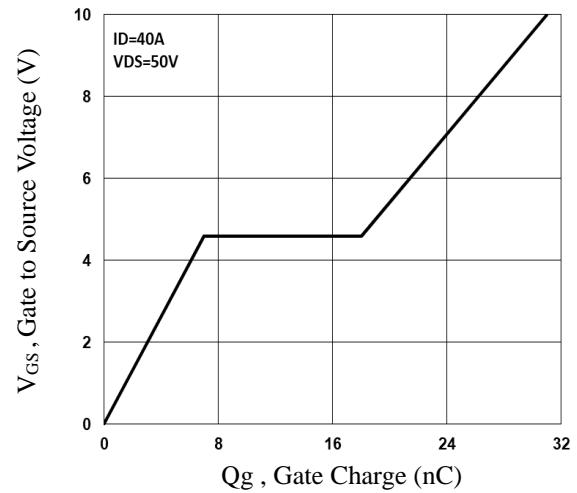


Fig.4 Gate Charge Characteristics

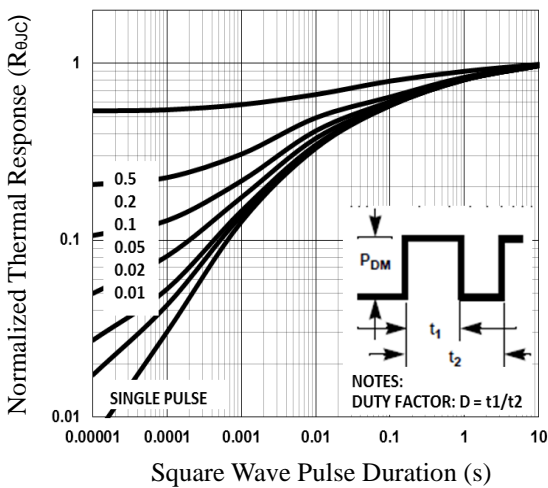


Fig.5 Normalized Transient Impedance

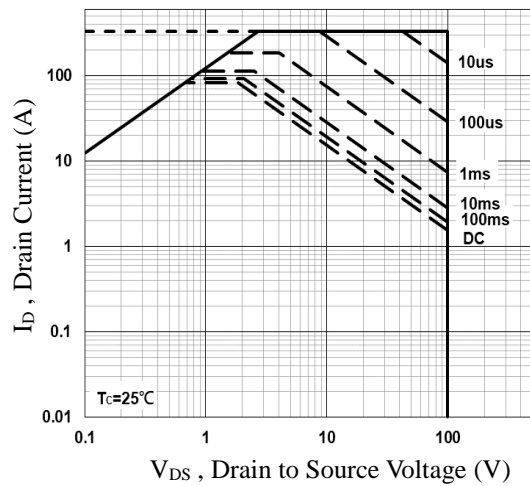


Fig.6 Maximum Safe Operation Area

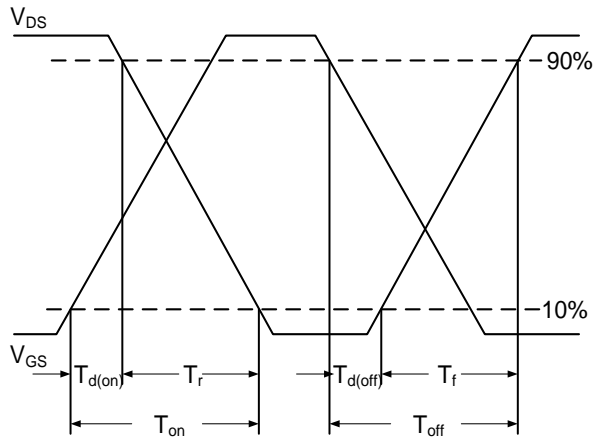


Fig.7 Switching Time Waveform

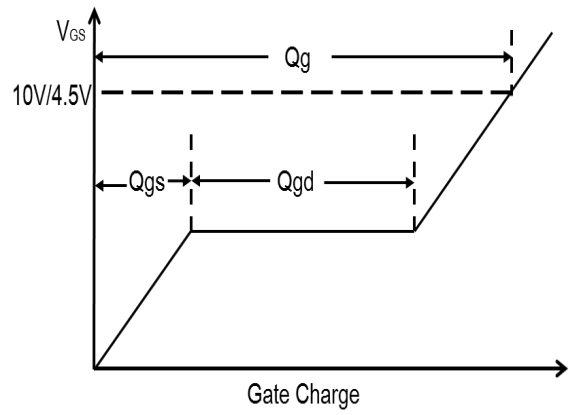
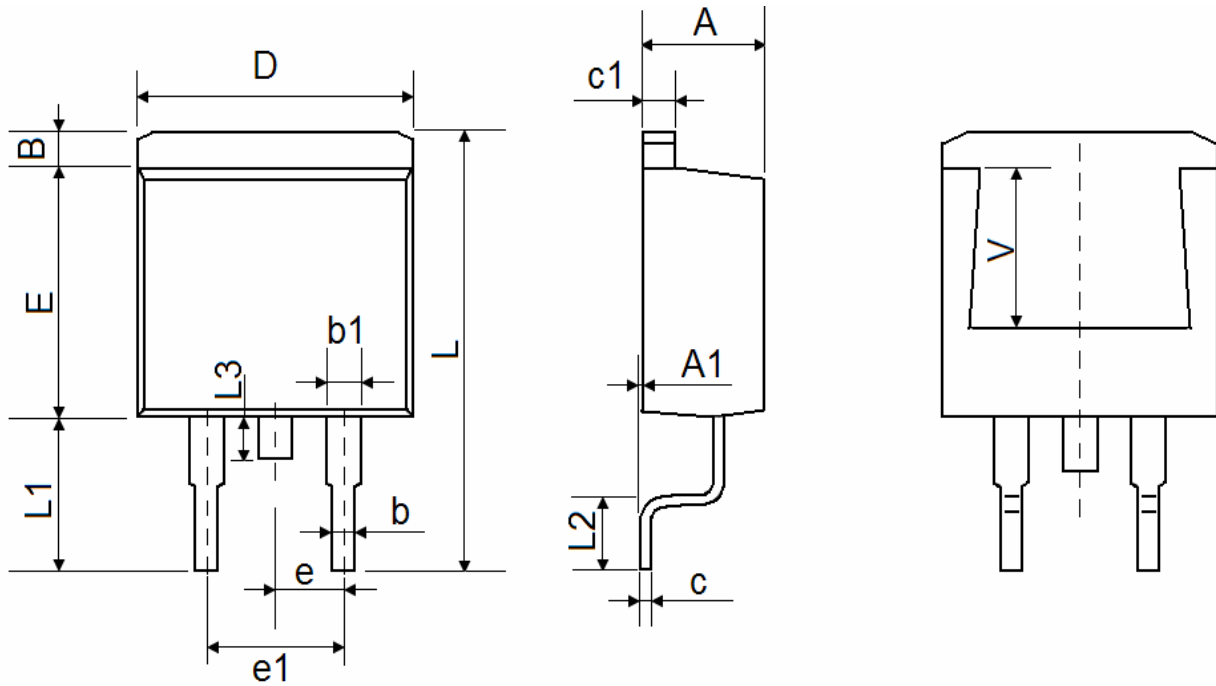


Fig.8 Gate Charge Waveform

TO-263 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	4.40	4.55	4.70	A1	0.00	0.07	0.15
B	1.00	1.20	1.40	b	0.65	0.80	0.95
b1	1.10	1.15	1.37	c	0.30	0.40	0.53
c1	1.10	1.25	1.37	D	9.80	10.00	10.40
E	8.50	8.80	9.20	e	2.54 REF		
e1	4.90	5.10	5.40	L	14.80	15.20	15.70
L1	5.00	5.25	5.60	L2	2.05	2.45	2.80
L3	1.20	1.50	1.80	V	5.60 REF		